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LIST OF ABBREVIATIONS

°C	Degree Celsius
Å	Angstrom
BL5.2	Beamline 5.2
EXAFS	Extended X-ray Absorption Fine Structure
E_0	Absorption edge
E_B	Binding Energy
eV	Electron-Volt
GIXRD	Gracing Incident X-ray Diffraction
h	Plank's Constant
I_e	Electron Current
I_p	Photon Current
LCF	Linear Combination Fitting
RGT	Reactive Gas-Timing
SEM	Scanning Electron Microstructure
SLRI	Synchrotron Light Research Institute
UV	Ultraviolet
VIS	Visible
XANES	X-ray Absorption Near Edge Structure
XAS	X-ray Absorption Spectroscopy
XRD	X-ray Diffraction
λ	Wavelength
σ^2	Debye-Waller factor
S_0^2	Scale Factor